

Low Voltage Standard Rectifier

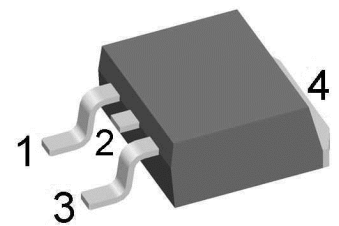
$$\begin{aligned} V_{RRM} &= 800 \text{ V} \\ I_{FAV} &= 20 \text{ A} \\ V_F &= 1.22 \text{ V} \end{aligned}$$

Single Diode

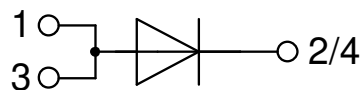
Part number

DLA20IM800PC

Marking on Product: DLA20IM800PC



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

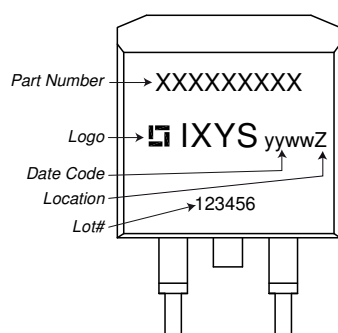
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				800	V
I_R	reverse current	$V_R = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			5	μA
		$V_R = 800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0.05	mA
V_F	forward voltage drop	$I_F = 20\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.25	V
		$I_F = 40\text{ A}$				1.49	V
		$I_F = 20\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.22	V
		$I_F = 40\text{ A}$				1.54	V
I_{FAV}	average forward current	$T_C = 140^{\circ}\text{C}$ rectangular	$T_{VJ} = 175^{\circ}\text{C}$ $d = 0.5$			20	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.88	V
r_F	slope resistance					17	m Ω
R_{thJC}	thermal resistance junction to case					1	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				150	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			200	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			215	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			170	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			185	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			200	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			190	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			145	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			140	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			7		pF

Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
F_c	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



Part description

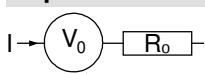
D = Diode
 L = Low Voltage Standard Rectifier
 A = (up to 1200V)
 20 = Current Rating [A]
 IM = Single Diode
 800 = Reverse Voltage [V]
 PC = TO-263AB (D2Pak) (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DLA20IM800PC-TTL	DLA20IM800PC	Tape & Reel	800	506475
Alternative	DLA20IM800PC-TUB	DLA20IM800PC	Tube	50	506628

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



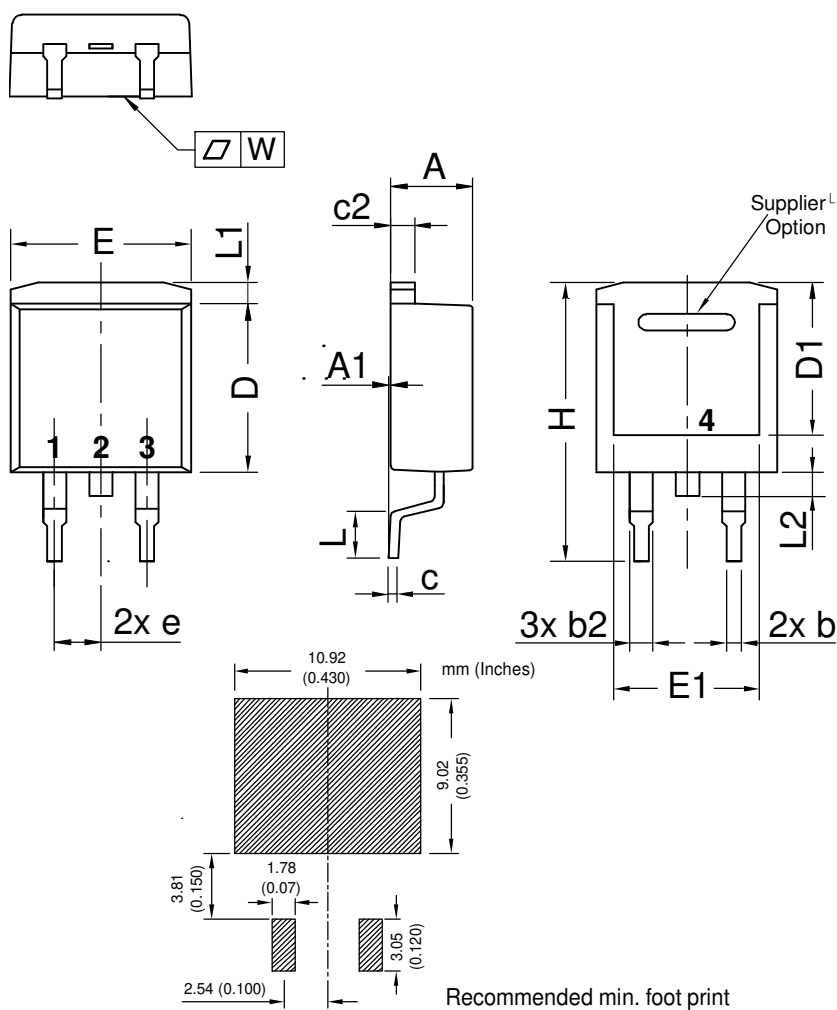
Rectifier

$V_{0\max}$ threshold voltage 0.88

$R_{0\max}$ slope resistance * 13

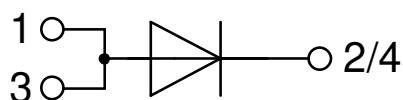
V

mΩ

Outlines TO-263 (D2Pak)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2.54 BSC		0.100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



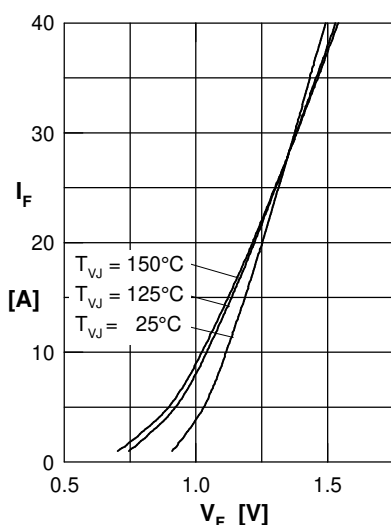
Rectifier


Fig. 1 Forward current versus voltage drop

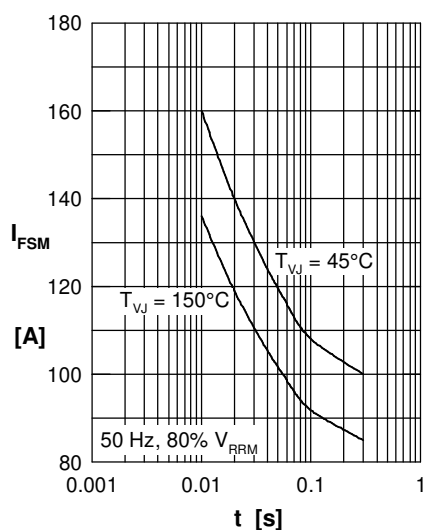


Fig. 2 Surge overload current

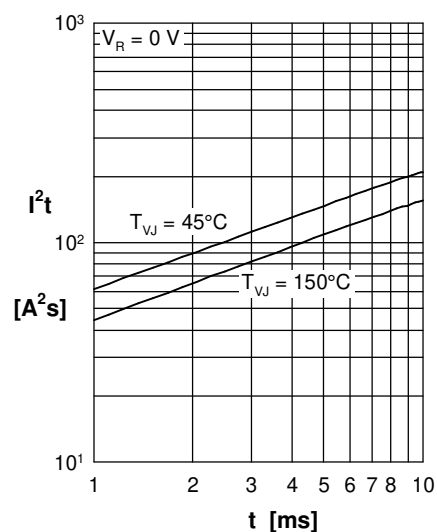
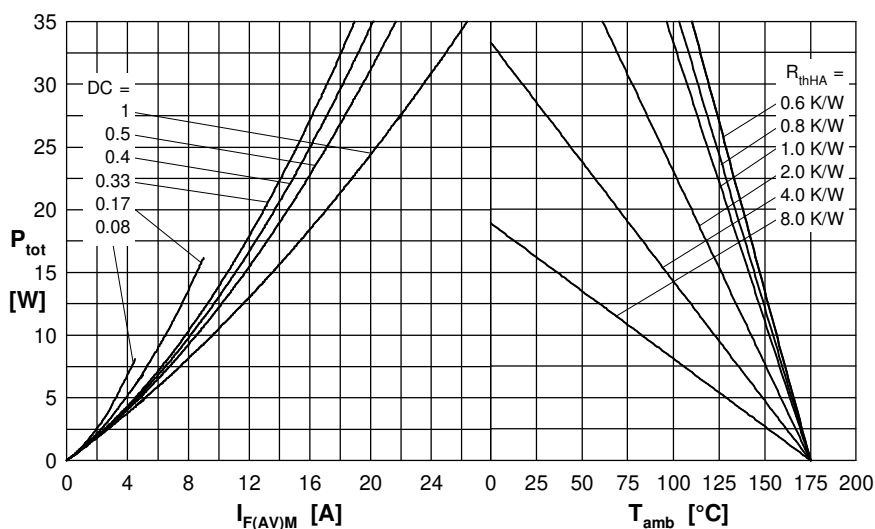

 Fig. 3 I^2t versus time


Fig. 4 Power dissipation versus direct output current and ambient temperature

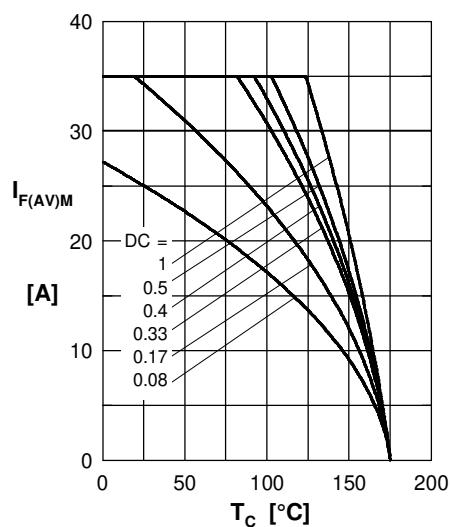


Fig. 5 Max. forward current vs. case temperature

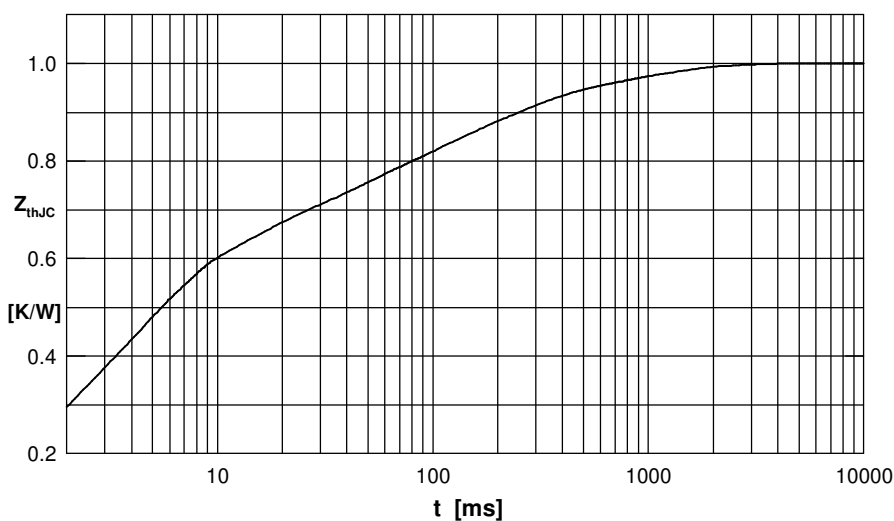


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.51	0.0035
2	0.06	0.0003
3	0.14	0.0250
4	0.09	0.8000
5	0.20	0.1400